

AMENDMENT UNDER 37 C.F.R. § 1.114(c)
U.S. Appln. No.: 10/606,859
Attorney Docket No.: Q76311

REMARKS

Claims 1-18 are cancelled without prejudice or disclaimer in this response. Claims 19-34 have been added. Claims 19-34 will be all the claims pending in application upon entry of the Amendment.

Support for the memory device of the new claims can be found on page 3, lines 12-14 of the specification and in the original claims. Applicants therefore submit that no new matter has been added.

Rejections of claims 1-18 under 35 U.S.C. § 102 or 103(a)

The rejections of claims 1-18 under 35 U.S.C. § 102 or 103(a) are moot in view of the cancellation of these claims.

New claims 19-34

Applicants submit that new independent claim 19 is novel and non-obvious over the cited references for the reasons discussed below.

Claim 19 recites a memory device comprising a quaternary metal oxide having a high dielectric constant (>320) and a low dielectric loss (<0.01) at high frequency (2.5 GHz).

None of the cited references teaches or suggests a memory device comprising such a dielectric material. For example, Nakamura et al (US 6,620,753), Kim et al (US 6,429,163), Nomura et al (US 5,312,517), Sano et al (US 5,510,305), Chazono et al (US 5,296,425), Chaput et al (US 5,017,534), and Hanke et al (US 4,054,532) are all directed to multilayer ceramic capacitors, and their dielectric properties at GHz frequency are never mentioned. Li et al (US 6,641,940) is directed to a low loss dielectric material for microwave applications, but also fails

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to disclose the application of quaternary metal oxide in memory devices. Therefore, it would not have been obvious to include such a quaternary metal oxide in a memory device.

Further, although Joe et al (US 6,096,593) teaches a memory device having a capacitor dielectric of ABO_3 (A=Ba, Sr, Pb, La; B=Zr, Ti), there is no teaching in Joe et al that would have suggested to an artisan that a memory device with a quaternary metal oxide could be prepared.

As none of the cited reference, when taken alone or in combination, teaches or suggests the features as set forth in claim 19, it is Applicants' belief claim 19 is allowable over the cited references. Insofar as claims 20-34 depend from claim 19, it is Applicants' belief that these claims are also allowable at least by virtue of their dependency.

Allowance is respectfully requested.

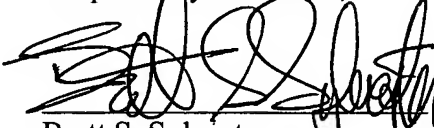
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Respectfully submitted,



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